

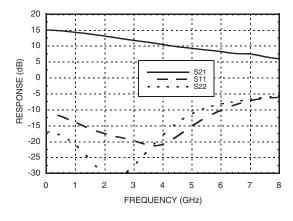
HMC479MP86 / 479MP86E

v03.0810

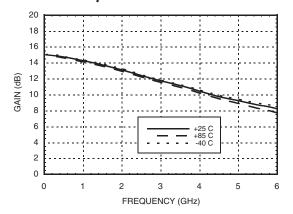


SiGe HBT GAIN BLOCK MMIC AMPLIFIER, DC - 5 GHz

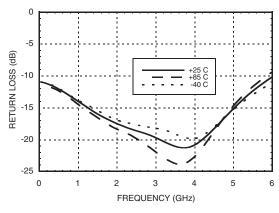
Broadband Gain & Return Loss



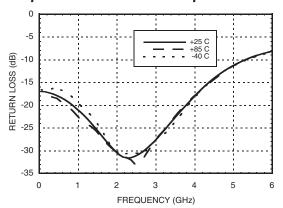
Gain vs. Temperature



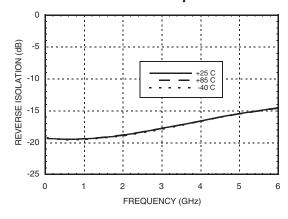
Input Return Loss vs. Temperature



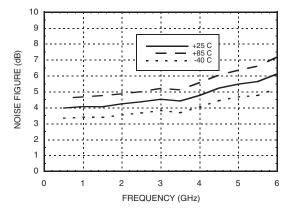
Output Return Loss vs. Temperature



Reverse Isolation vs. Temperature



Noise Figure vs. Temperature



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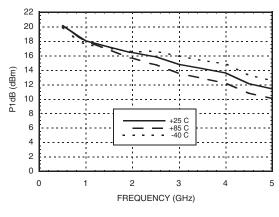


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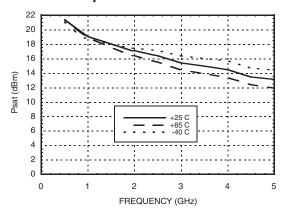


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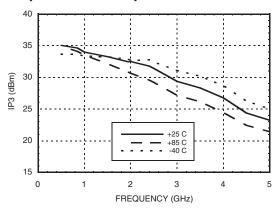
P1dB vs. Temperature



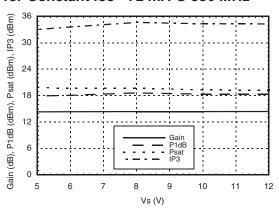
Psat vs. Temperature



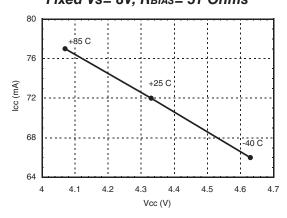
Output IP3 vs. Temperature



Gain, Power & OIP3 vs. Supply Voltage for Constant Icc= 72 mA @ 850 MHz



Vcc vs. Icc Over Temperature for Fixed Vs= 8V, RBIAS= 51 Ohms





HMC479MP86 / 479MP86E

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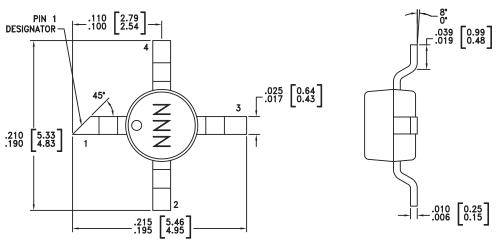
SiGe HBT GAIN BLOCK MMIC AMPLIFIER, DC - 5 GHz

Absolute Maximum Ratings

Collector Bias Voltage (Vcc)	+6 Vdc	
Collector Bias Current (Icc)	100 mA	
RF Input Power (RFIN)(Vcc = +4.3 Vdc)	+17 dBm	
Junction Temperature	150 °C	
Continuous Pdiss (T = 85 °C) (derate 10.8 mW/°C above 85 °C)	0.702 W	
Thermal Resistance (junction to lead)	92.6 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	



Outline Drawing



.090 [2.29] (3) - .080 [2.03] - .080 [2.03] - .085 [1.65] (1.40] (1.19) (1.19) (1.19) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.18) (1.007) (1.007) (1.18) (1.007) (1.00

NOTES

- 1. LEADFRAME MATERIAL: COPPER ALLOY
- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- ⚠ DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
- 4. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.
- 5. THE MICRO-P PACKAGE IS DIMENSIONALLY COMPATIBLE WITH THE "MICRO-X PACKAGE"

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking
HMC479MP86	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	479
HMC479MP86E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	<u>479</u>

^[1] Max peak reflow temperature of 235 $^{\circ}\text{C}$

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^[2] Max peak reflow temperature of 260 $^{\circ}\text{C}$



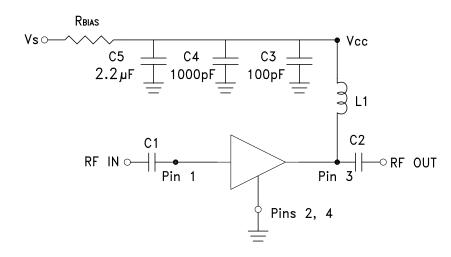
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SiGe HBT GAIN BLOCK MMIC AMPLIFIER, DC - 5 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1	RFIN	This pin is DC coupled. An off chip DC blocking capacitor is required.	RFOUT
3	RFOUT	RF output and DC Bias (Vcc) for the output stage.	
2, 4	GND	These pins must be connected to RF/DC ground.	GND =

Application Circuit



Recommended Bias Resistor Values for Icc= 72 mA, Rbias= (Vs - Vcc) / Icc

Supply Voltage (Vs)	5V	6V	8V	10V	12V
RBIAS VALUE	13 Ω	27 Ω	51 Ω	82 Ω	110 Ω
RBIAS POWER RATING	1/8 W	1/4 W	1/2 W	1/2 W	1 W

Note:

- External blocking capacitors are required on RFIN and RFOUT.
- 2. RBIAS provides DC bias stability over temperature.

Recommended Component Values for Key Application Frequencies

Component	Frequency (MHz)						
Component	50	900	1900	2200	2400	3500	5000
L1	270 nH	56 nH	18 nH	18 nH	15 nH	8.2 nH	6.8 nH
C1, C2	0.01 μF	100 pF					

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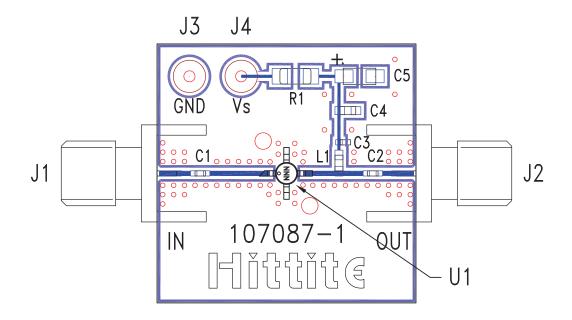
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Evaluation PCB



List of Materials for Evaluation PCB 107489 [1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3 - J4	DC Pin
C1, C2	Capacitor, 0402 Pkg.
C3	100 pF Capacitor, 0402 Pkg.
C4	1000 pF Capacitor, 0603 Pkg.
C5	2.2 µF Capacitor, Tantalum
R1	Resistor, 1210 Pkg.
L1	Inductor, 0603 Pkg.
U1	HMC479MP86 / HMC479MP86E
PCB [2]	107087 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.